

Engineering electrodeposited ZnO films and their memristive switching performance

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Reproducibility of the Zn and O composition as a function of film processing

In order to verify the reproducibility of the Zn and O composition as a function of film processing, we fabricated five different samples for each type of ZnO films (SL, ECD 1000s, ECD 3000s, SL & ECD 500s, SL & ECD 1000s). Figure S1 shows the average of Zn and O elemental composition. The tests were performed on five times.

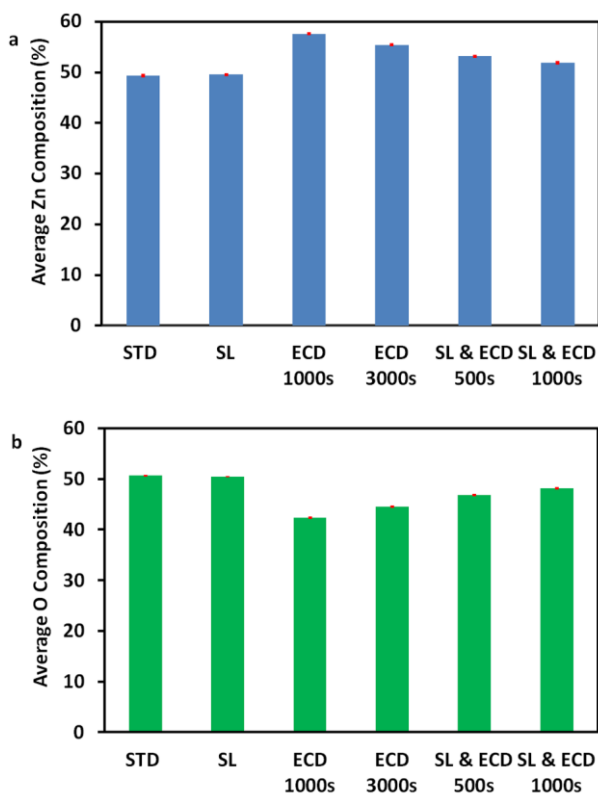


Fig. S1 Average of Zn and O elemental compositions for six different types of ZnO (standard ZnO target and films). The tests were performed on five similarly fabricated samples. The standard deviation was < 10%.